

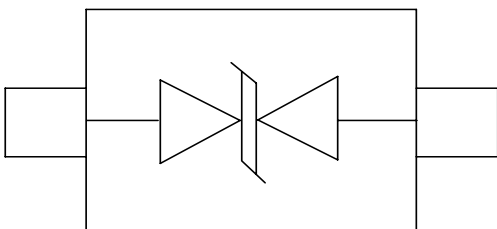
Description

The AU0581D3H is a bi-directional high power TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The AU0581D3H complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into an ultra-small lead-free SOD-323 package. The small size and high ESD surge protection make AU0581D3H an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Small SOD-323 package
- Protects one data or power line
- Working Voltage: 5V
- High peak pulse current capability
- Ultra low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 132A (8/20 μs)
- RoHS Compliant

Dimensions and Pin Configuration



Circuit Diagram

Mechanical Characteristics

- Package: SOD-323
- Lead Finish: Sn
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Mobile Phones and Accessories
- Battery Protection
- USB VBus
- Power Line Protection
- Hand Held Portable Applications

Marking Information



58DH: Device Marking

Ordering Information

Part Number	Marking	Packaging	Reel Size
AU0581D3H	58DH	3000/Tape & Reel	7 inch

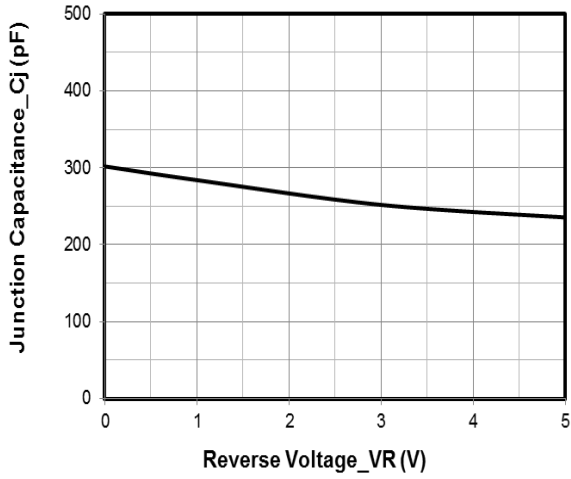
Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	2376	W
Peak Pulse Current (8/20 μs)	Ipp	132	A
ESD per IEC 61000-4-2 (Air)	VESD	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	TJ	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^\circ\text{C}$

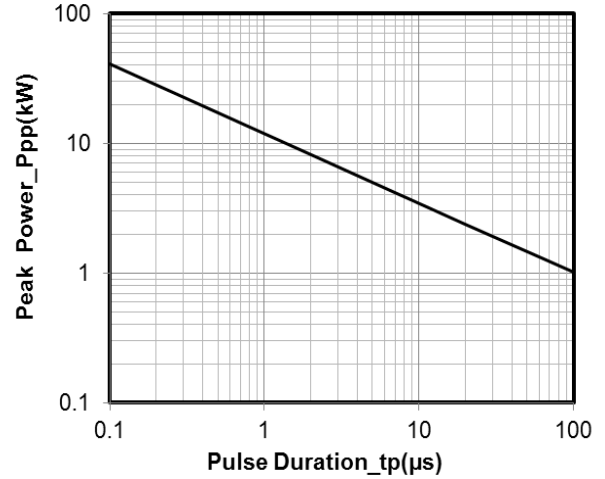
Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 5V
Clamping Voltage	VC			9	V	I _{PP} = 20A (8 x 20 μs pulse)
Clamping Voltage	VC			18	V	I _{PP} = 132A (8 x 20 μs pulse)
Junction Capacitance	CJ		300		pF	VR = 0V, f = 1MHz

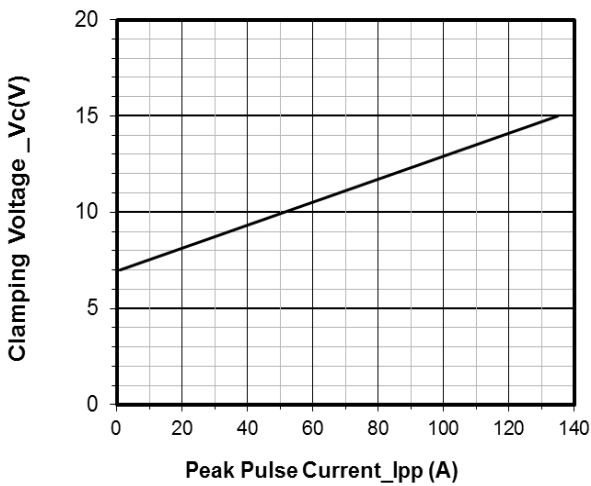
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



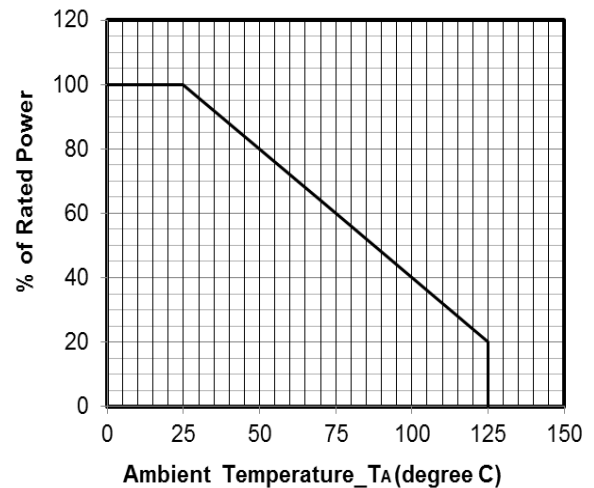
Junction Capacitance vs. Reverse Voltage



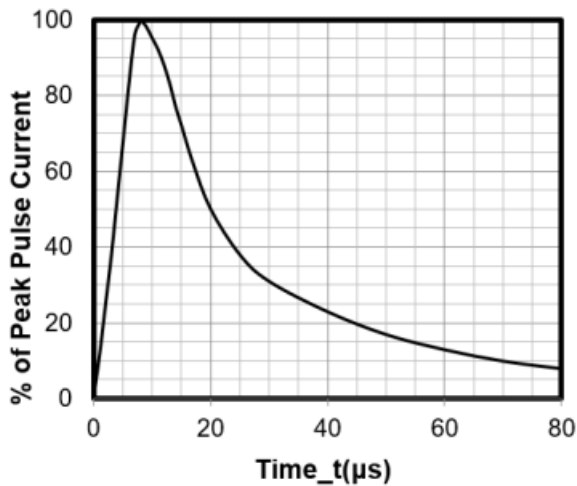
Peak Pulse Power vs. Pulse Time



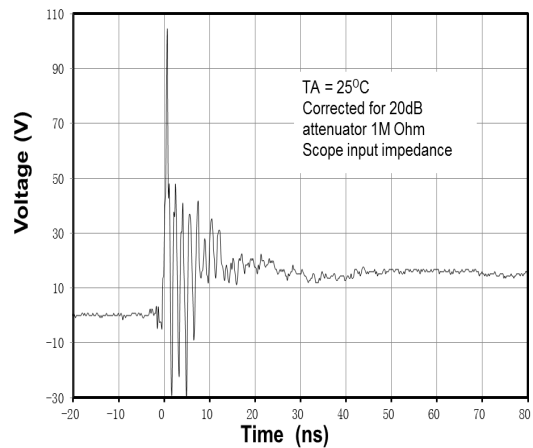
Clamping Voltage vs. Peak Pulse Current



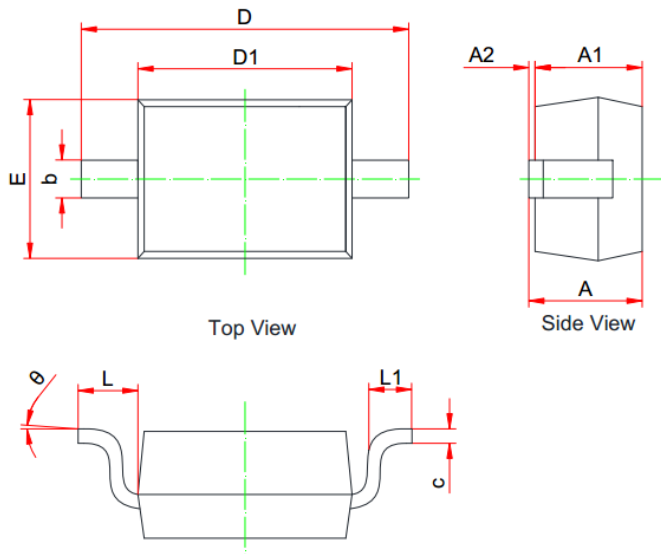
Power Derating Curve



8 X 20μs Pulse Waveform



ESD Clamping Voltage
8 kV Contact per IEC61000-4-2

SOD-323 Package Outline Drawing


	MILLIMETERS		
	MIN	NOM	MAX
A	0.800	--	1.100
A1	0.800	--	0.900
A2	0.000	--	0.100
b	0.250	--	0.400
c	0.080	--	0.177
D1	1.600	1.700	1.800
D	2.300	--	2.800
E	1.150	--	1.400
L	0.475REF		
L1	0.100	--	0.500
Θ	0°	--	8°

Suggested Land Pattern

Unit: mm
Contact Information

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